

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	598143	diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49
L2	67345	(esd (electrostatic electro adj static) adj (discharge protect\$4) ) protect\$4 adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49
L3	4210	"no gate" "without gate" non adj.gate\$2 nongate\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49
L4	222	L1 with L3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49
L5	79	L4 and L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49
L6	440	planar adj L1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49
L7	10	L6 and L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49
L8	89	L5 L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 09:58
L9	82153	fifth.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 09:59
L10	215257	(concentration impurity dop\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:00

L11	1761	9 with 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:00
L12	87534	diode.clm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:00
L13	54	11 same 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:00
L14	170	11 and 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:01
L15	5855064	carrier conductivity type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:01
L16	950	11 with 15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:01
L17	43	16 same 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:22
L18	2	pppnn ppnnnn nnnpp npppp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:24
L19	955	p near p near p near n near n p near p near n near n near n	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:23
L20	41	1 with 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:24

L21	6	20 and 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:24
S1	0	10/753914	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:07
S2	1	09/948877	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:07
S3	1736	"KONINKLIJKE PHILIPS".as.	USPAT	OR	ON	2003/08/19 13:35
S4	0	10/778180	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:34
S5	1	10/781879	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:10
S6	20692	(esd (electrostatic electro adj static) adj (discharge protect\$4) )	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:41
S7	583152	diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:23
S8	427636	thin adj film\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:35
S9	2800	S7 near2 S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:36
S10	18	S9 same S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:41

S11	47	S9 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:41
S12	29	S11 not S10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:42
S13	644	S9.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:43
S14	1	S12 and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:44
S15	255807	S7.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:44
S16	5	S12 and S15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:00
S17	139190	intrinsic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:01
S18	1195697	"p-i-n" pin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:10
S19	11014	S18 adj S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:11
S20	93	S8 with S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:12

S21	39	S20 and S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:18
S22	1374	ppn pnn	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:19
S23	5	S22 adj3 S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:21
S24	3113	ppn pnn p-p-n p-n-n n-n-p n-p-p npp nnp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:24
S25	8	S24 adj3 S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:29
S26	83504	(four multiple) adj layer\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:31
S27	425	S26 adj S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:30
S28	4	S8 with S27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:30
S29	20842	(four ) adj layer\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:31
S30	419	S29 adj S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:31

S31	43	S30 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:38
S32	10	S30 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:32
S33	1	S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:31
S34	2	("6118154").URPN	USPAT	OR	ON	2005/04/25 15:46
S35	10	("3555374"   "4282556"   "4745450"   "4893159"   "4989057"   "5440161"   "5510728"   "5610426"   "5841172").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 15:48
S36	6	S35 and S7	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 15:48
S37	7	("3512058"   "3712995"   "3947727"   "4037140"   "4131928").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 16:05
S38	11	S16 S37	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/26 07:21
S39	378123	transistor	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 16:15
S40	601	(S8 adj S39 tft) adj process	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 16:16
S41	10360986	@pd <"20000101"	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 16:16
S42	116	S40 and S41	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 16:38
S43	22	S40.ab.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 16:44
S44	6	S6 and S40	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 18:42
S45	35080	(breakdown break adj down) adj voltage	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 18:42

S46	80	S19 with S45	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/25 18:42
S47	80	p+nn+ p+pn n+pp+ n+np p+-n-n+ p+-p-n n+-p-p+ n+-n-p	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/26 07:23
S48	583429	diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:23
S49	3117	ppn pnn p-p-n p-n-n n-n-p n-p-p npp nnp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:24
S50	3169	S47 S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:24
S51	14	S50 adj S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:24
S52	65607	(esd (electrostatic electro adj static) adj (discharge protect\$4) ) protect\$4 adj circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:42
S53	3619	"no gate" "without gate"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 08:04
S54	179	S48 with S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:43
S55	57	S54 and S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 07:44
S56	5	("4989057"   "5610790"   "6404269"   "6496341"   "6608744").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/26 07:57

S57	4075	"no gate" "without gate" non adj gate\$2 nongate\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 08:05
S58	205	S48 with S57	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 08:05
S59	63	S58 and S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 08:06
S60	6	S59 not S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 08:09
S61	434	planar adj S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 08:10
S62	10	S61 and S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 08:13
S63	73	S59 S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:49